

# Technical Data Sheet

## 1.5mm Side Looking Infrared Emitting Diode

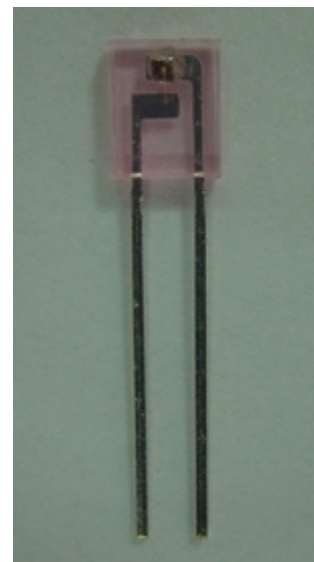
### SIR908-7P-R

#### ■ Features

- Low forward voltage
- Peak wavelength  $\lambda_p=875\text{nm}$
- High reliability

#### ■ Descriptions

The SIR908-7P-R is a GaAlAs infrared emitting diode. The miniature side-facing device has a chip that emits radiation from the side of the pink package.



#### ■ Applications

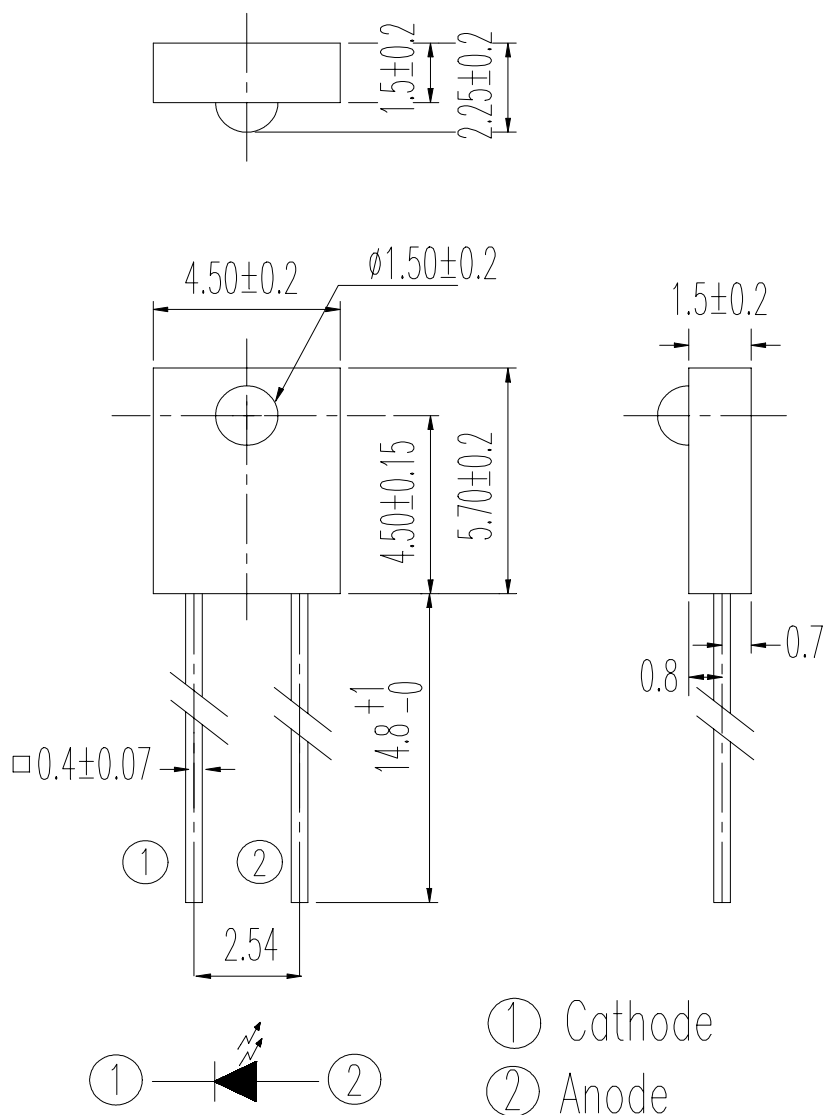
- Optoelectronic switch
- Photo interrupter

#### ■ Device Selection Guide

LED Part No.	Chip	Lens Color
	Material	
SIR	GaAlAs	PINK

Device No:DIS-090-078

■ **Package Dimensions**



**Notes:** 1.All dimensions are in millimeters  
2.Tolerances unless dimensions  $\pm 0.1\text{mm}$

**Absolute Maximum Ratings (Ta=25°C)**

Parameter	Symbol	Rating	Units
Continuous Forward Current	I <sub>F</sub>	60	mA
Peak Forward Current(*)	I <sub>FP</sub>	1.0	A
Reverse Voltage	V <sub>R</sub>	5	V
Operating Temperature	T <sub>opr</sub>	-25 ~ +85	°C
Storage Temperature	T <sub>stg</sub>	-40 ~ +85	°C
Soldering Temperature	T <sub>sol</sub>	260	°C
Power Dissipation at(or below) 25°C Free Air Temperature	P <sub>d</sub>	150	mW

**Notes:** \*1: tw=100 μ SEC., Duty cycle=1%

**Electro-Optical Characteristics (Ta=25°C)**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Units
Collector current	I <sub>C(ON)</sub>	V <sub>CE</sub> =3.5V, I <sub>F</sub> =4mA	300	--	1300	μ A
Peak Wavelength	λ <sub>p</sub>	I <sub>F</sub> =20mA	--	875	--	nm
Spectral Bandwidth	Δ λ	I <sub>F</sub> =20mA	--	50	--	nm
Forward Voltage	V <sub>F</sub>	I <sub>F</sub> =20mA	--	1.3	1.6	V
		I <sub>F</sub> =100mA, t <sub>p</sub> =100 μ s, t <sub>p</sub> /T=0.01	--	1.4	1.8	
		I <sub>F</sub> =1A, t <sub>p</sub> =100 μ s, t <sub>p</sub> /T=0.01	--	2.6	4.0	
Reverse Current	I <sub>R</sub>	V <sub>R</sub> =5V	--	--	10	μ A
View Angle	2 θ 1/2	I <sub>F</sub> =20mA	--	50	--	deg

## Typical Electro-Optical Characteristics Curves

Fig. 1 Forward Current vs. Ambient Temperature

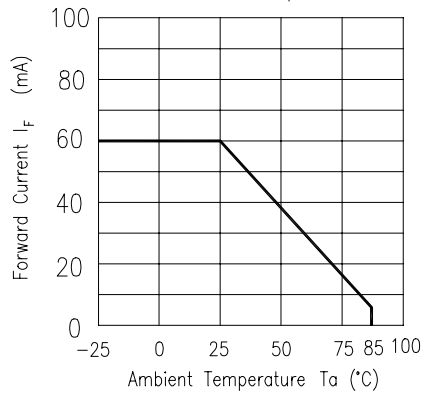


Fig. 2 Spectral Distribution

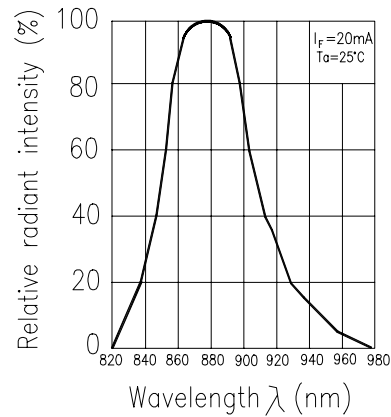


Fig. 3 Peak Emission Wavelength vs. Ambient Temperature

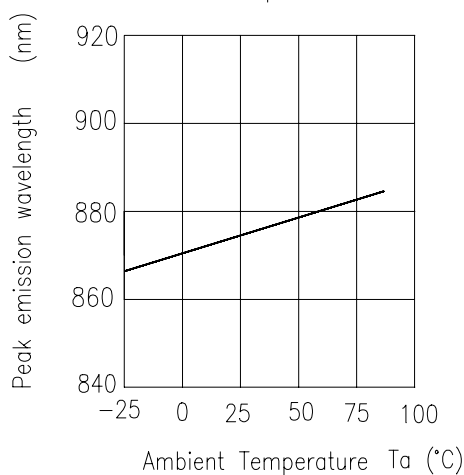


Fig. 4 Forward Current vs. Forward Voltage

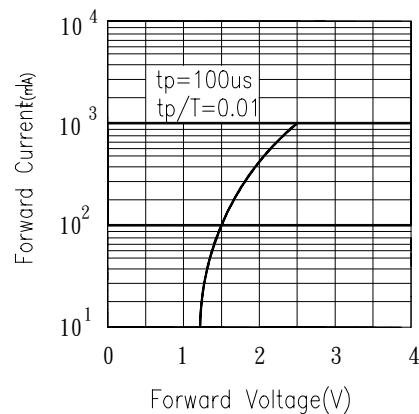


Fig. 5 Forward Current vs. Ambient Temperature

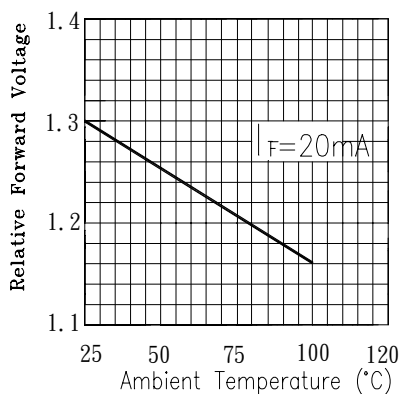
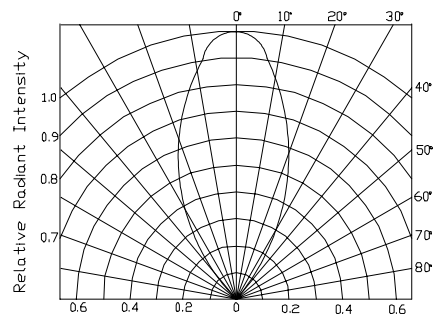


Fig. 6 Relative Radiant Intensity vs. Angular Displacement

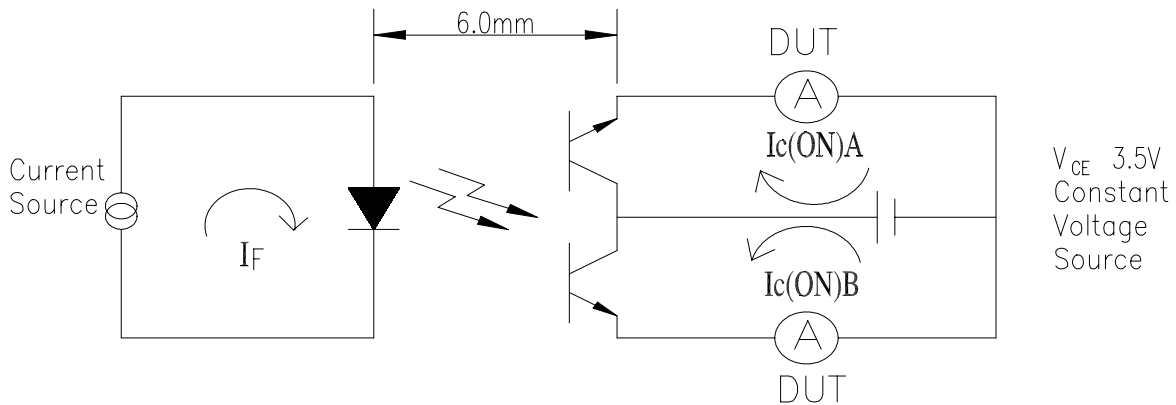


Device No:DIS-090-078

■ **Test Method For  $I_{C(ON)}$ :**

Condition:  $I_F=4mA$

The intensity testing method for infrared emitting diode



■ **To Distinguish Intensity:**

Condition:  $V_{CE}=3.5V$ ,  $I_F=4mA$

UNIT:  $\mu A$

Bin Number	7-2	7-1	6-2	6-1
Min	300	340	450	630
Max	450	560	770	1300

### Reliability Test Item And Condition

The reliability of products shall be satisfied with items listed below.

Confidence level : 90%

LTPD : 10%

NO.	Item	Test Conditions	Test Hours/ Cycles	Sample Sizes	Failure Judgment Criteria	Ac/Re
1	Solder Heat	TEMP. : $260^{\circ}\text{C} \pm 5^{\circ}\text{C}$	5secs	22pcs	$I_R \geq U \times 2$	0/1
2	Temperature Cycle	H : $+85^{\circ}\text{C}$ 30mins <div style="text-align: center;"> <math>\updownarrow</math>  5mins  <math>\updownarrow</math>  L : <math>-55^{\circ}\text{C}</math> 30mins </div>	50 Cycles	22pcs	$I_{C(ON)} \leq L \times 0.8$ $V_F \geq U \times 1.3$	0/1
3	Thermal Shock	H : $+100^{\circ}\text{C}$ 5mins <div style="text-align: center;"> <math>\updownarrow</math>  10secs  <math>\updownarrow</math>  L : <math>-10^{\circ}\text{C}</math> 5mins </div>	50 Cycles	22pcs	U : Upper Specification	0/1
4	High Temperature Storage	TEMP. : $+100^{\circ}\text{C}$	1000 hrs	22pcs	Limit	0/1
5	Low Temperature Storage	TEMP. : $-55^{\circ}\text{C}$	1000 hrs	22pcs	L : Lower Specification	0/1
6	DC Operating Life	$I_F = 20\text{mA}$	1000 hrs	22pcs	Limit	0/1
7	High Temperature/ High Humidity	$85^{\circ}\text{C}$ / 85% R.H	1000 hrs	22pcs		0/1

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